



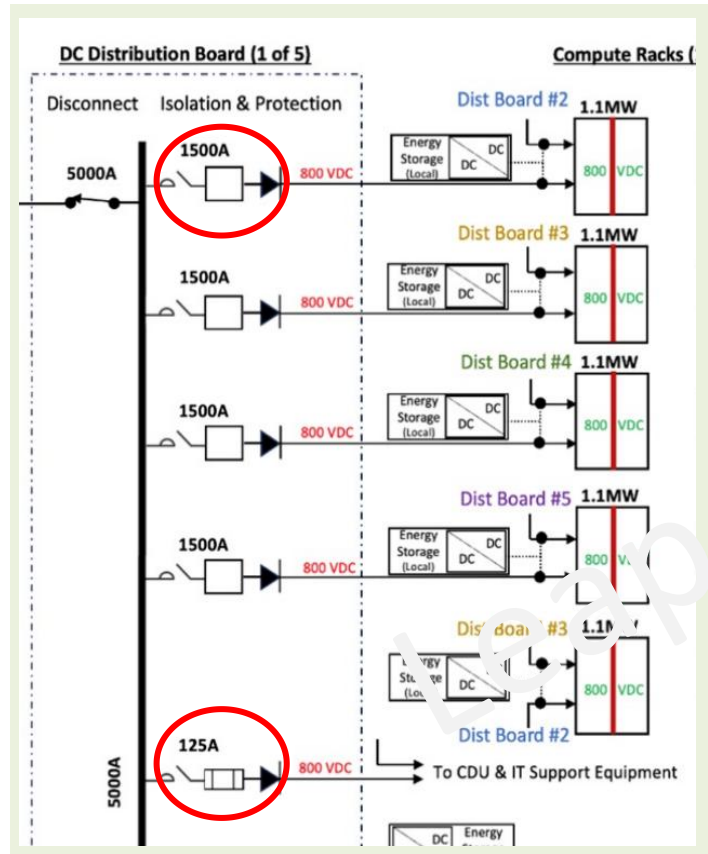
LPS SSCB promoting list

2026年8月20日

1. Why SSCB, and what's SSCB

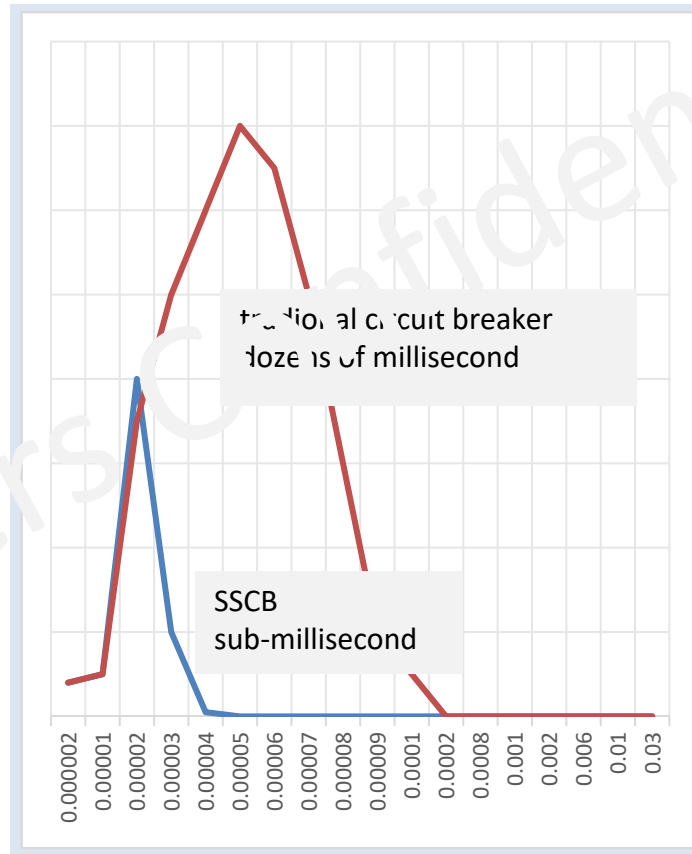
We see challenges in currently applications

High power

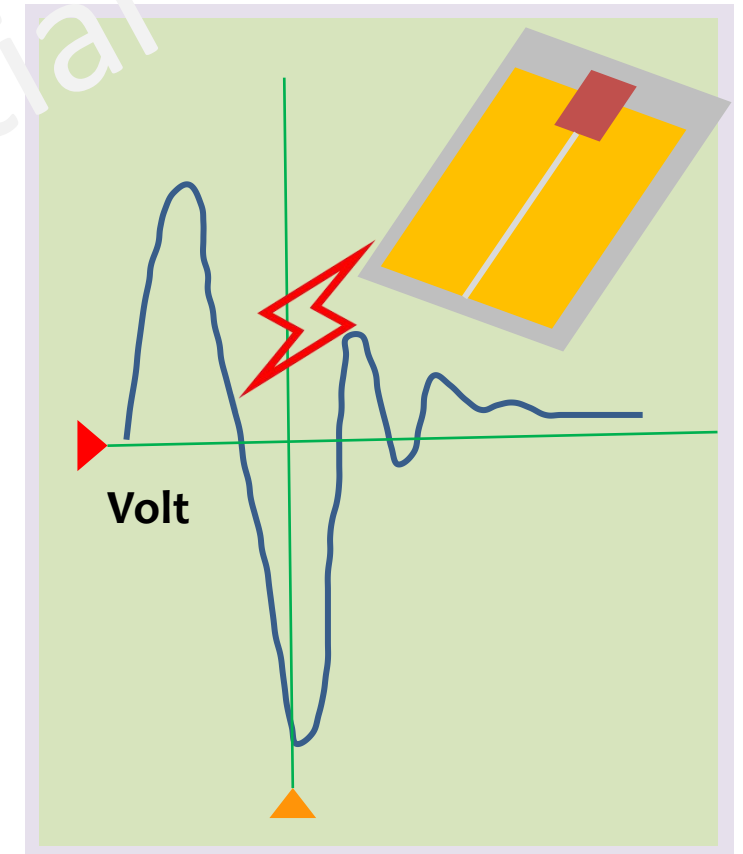


*来源 Siemens

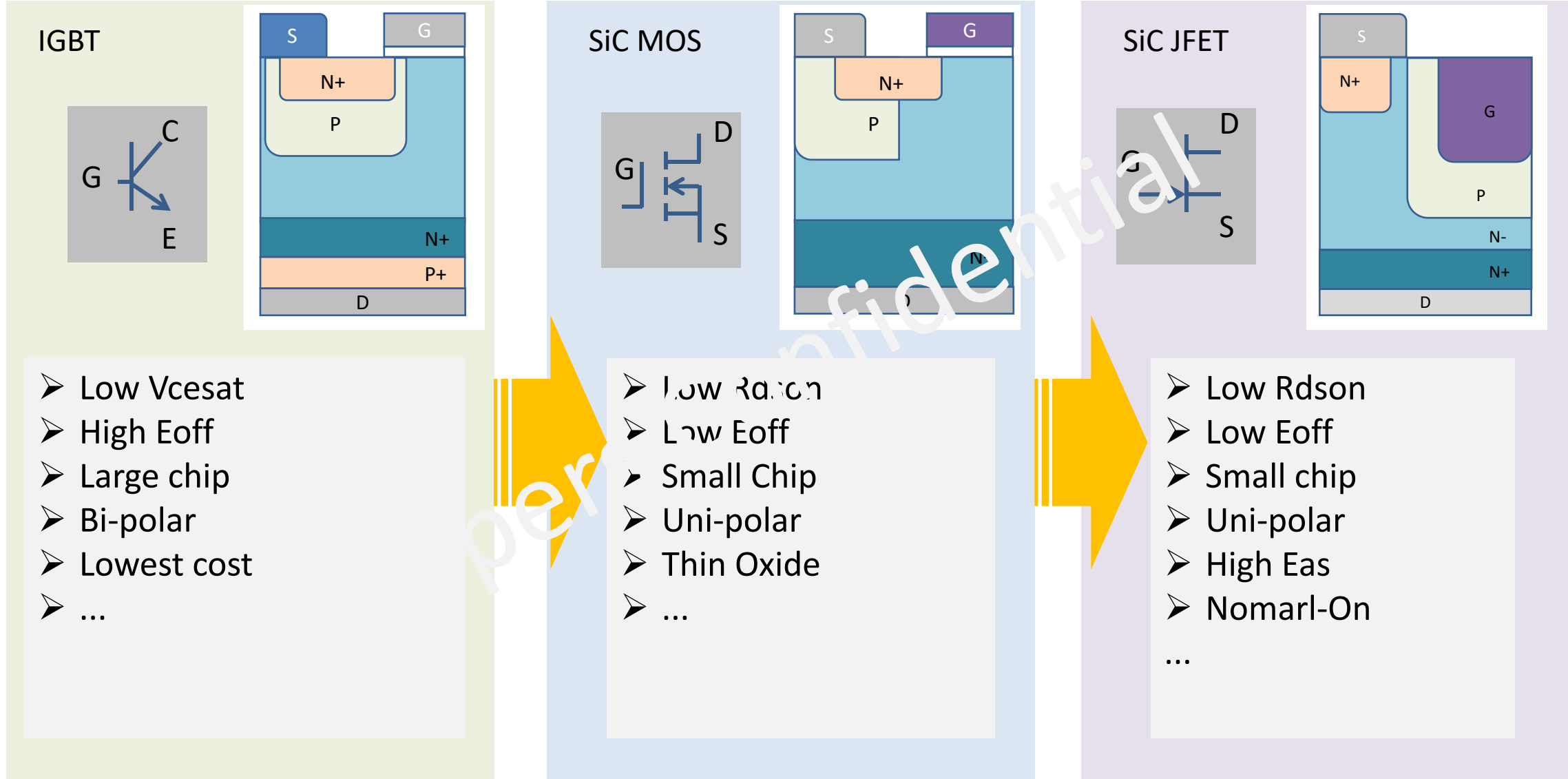
Fast response



Reliable

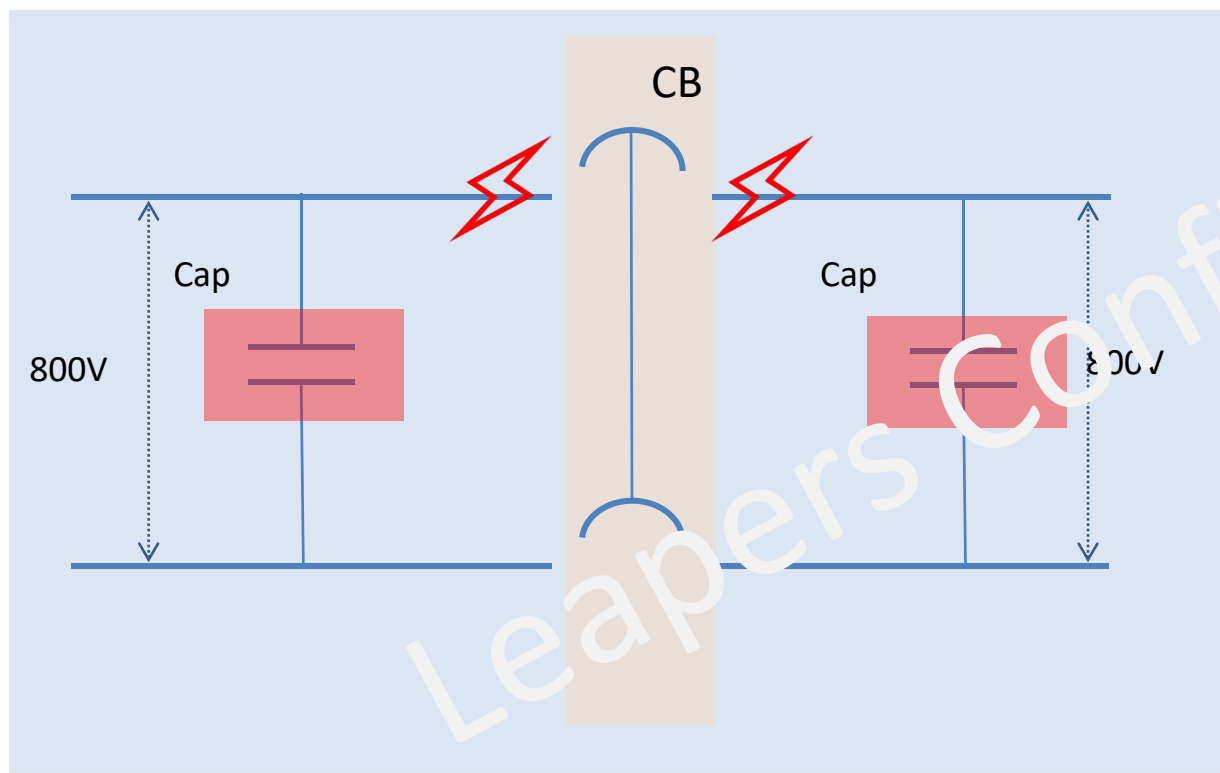


2. Trend of SSCB application



3. Leapers support your SSCB design with cutting edge technology and best quality

Capacitive load is most seen in AIDC and HVDC applications (more capacitors are used to ensure PF)



Advanced power devices should handle 'surge' current in 'SUB-millisecond'

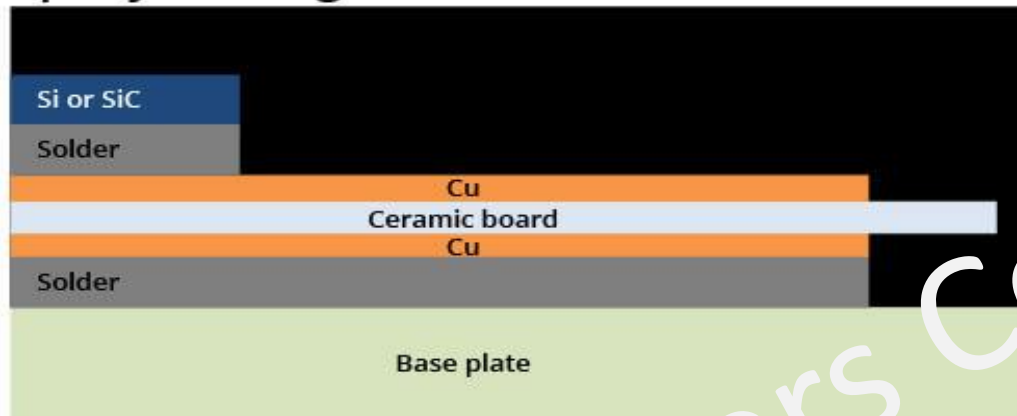
Linear operation area is preferred to

4. Challenges of SSCB in terms of power module design

Stable stage

Continuous large current flow through semiconductor

Epoxy Potting



Leapers utilize mature Epoxy Potting technology

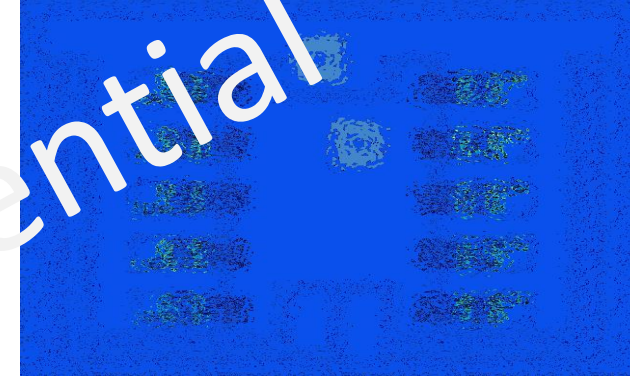
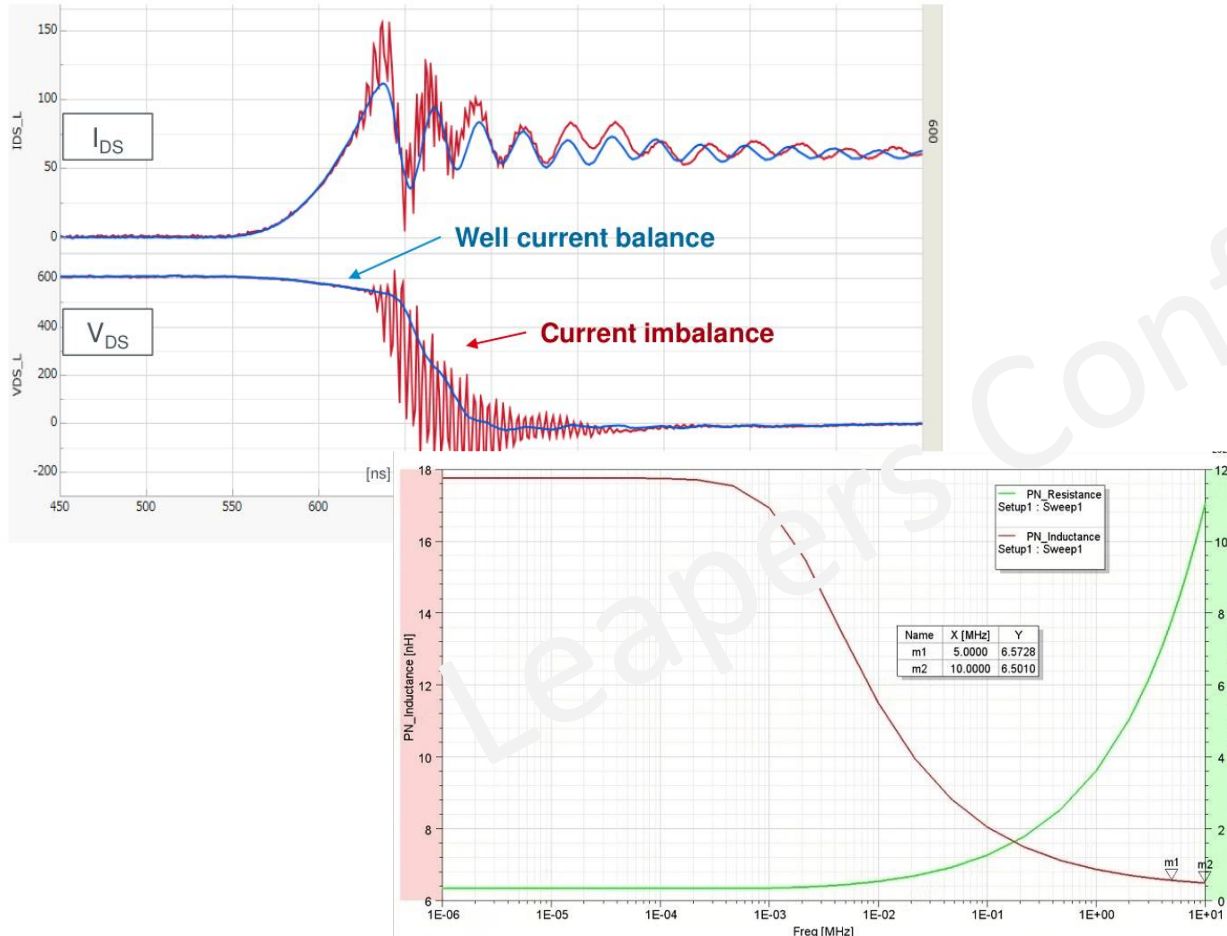
- High Tg epoxy resin up to 250°C
- Even thermal distribution in stable stage
- Along with optimized bonding technology the module can reach upto >110k PCsec cycle
- Continuous current flow devices cause heating up ($I^2 \cdot R$, $V_{cesat} \cdot I$)



4. Challenges of SSCB in terms of power module design

Cutting-off event

How to reach out unique performance of each chip in harsh conditon

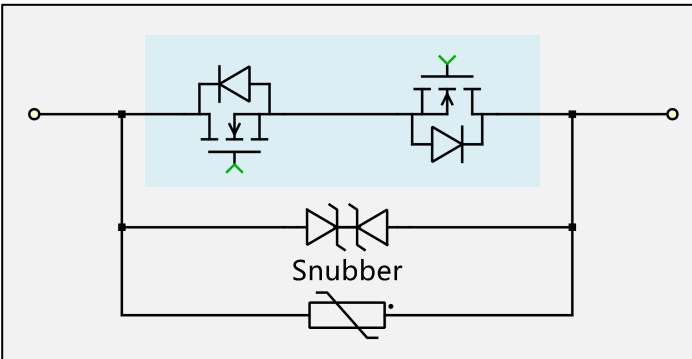


Leapers utilize experienced elaborate layout

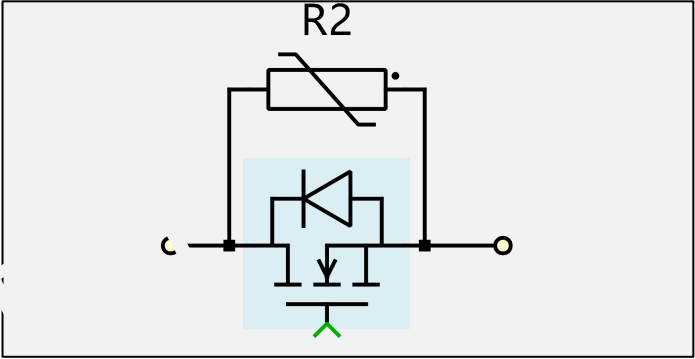
- Fully expand current rating, match market demand (numerous chips are paralleled)
- Higher current capability enable both main and branch application
- Optimized layout design (superior L_s , minimum less than 5nH)

4. Leapers support your SSCB design with cutting edge technology and best quality

LDP series



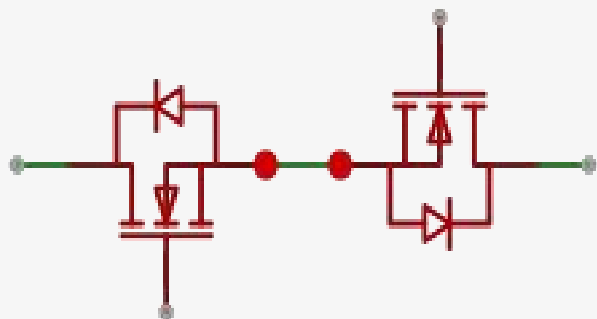
Common Source 'C-S' option



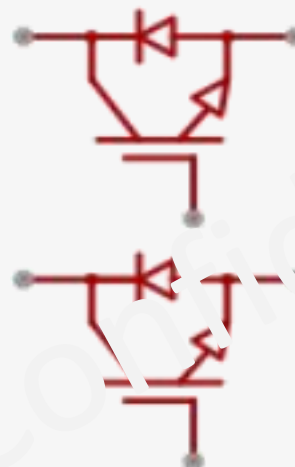
Single device option

IHV series

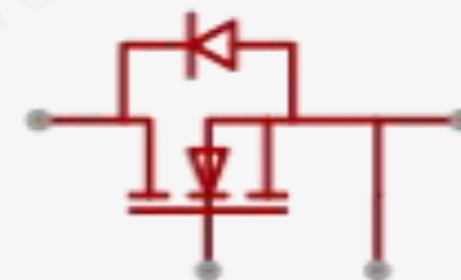
Volt	Rdson/ mR	Pkg	Configuration
1200V	450A	ED3	C-S, IGBT
1200V	600A	ED3	C-S, IGBT
1700V	2mR	ED3	C-S, SiC MOS
1700V	1.8mR	ED3	C-S, SiC JFET
1700V	0.8mR	IHV	Single Device, SiC MOS
1700V	0.3mR	IHV	Single Device, SiC MOS
More	tbd	tbd	tbd



Option 1 - 'C-S'
Common-source



Option 2. 'D-D'
Dual device



Option 3. 'S-D'
Single device

Leapers' integration solution for SSCB

产品型号	电压	电流/内阻 (Single Switch)	配置	封装	备注
DFI900***17***	1700V	900A	D-D	ED3	IGBT
DFS0D3***17***	1700V	0.3mR	S-D	IHV	SiC MOS
DFS01***14***	1400V	1mR	C-S	ED3	SiC MOS
DFS0D5***12***	1200V	0.5mR	C-S	ED3	SiC MOS
DFS0D4***12***	1200V	0.4mR	C-S	ED3	SiC MOS
DFS0D7***12***	1200V	0.7mR	C-S	ED3	SiC MOS
DFGoD9***12***	1200V	0.9mR	C-S	ED3	SiC JFET (Automotive grade)
DFS01***23***	2300V	1mR (Target)	S-D	t.b.d	SiC MOS



ED3 series



IHV series

THANKS

—— 新一代耐用型功率模块及应用专家 ——



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